



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

2SK4065 — General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)} = 4.6\text{m}\Omega$ (typ.)
- Input capacitance $C_{iss} = 12200\text{pF}$ (typ.)
- 4V drive

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

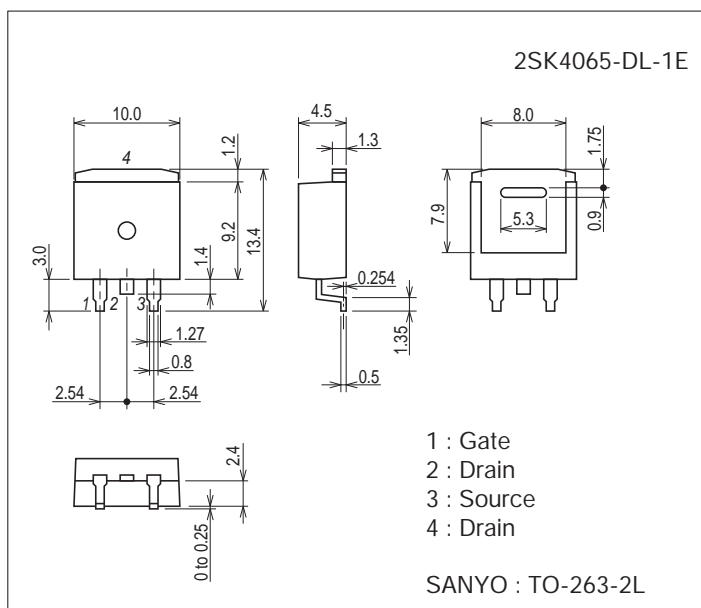
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		75	V
Gate-to-Source Voltage	V_{GS}		± 20	V
Drain Current (DC)	I_D		100	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	400	A
Allowable Power Dissipation	P_D		1.65	W
		$T_c = 25^\circ\text{C}$	90	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Avalanche Energy (Single Pulse) *1	EAS		735	mJ
Avalanche Current *2	I_{AV}		70	A

Note : *1 $V_{DD} = 30\text{V}$, $L = 200\mu\text{H}$, $I_{AV} = 70\text{A}$ (Fig.1)*2 $L \leq 200\mu\text{H}$, single pulse

Package Dimensions

unit : mm (typ)

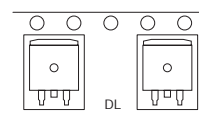
7535-001



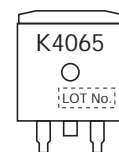
Product & Package Information

- Package : TO-263-2L
- JEITA, JEDEC : SC-83, TO-263
- Minimum Packing Quantity : 800 pcs./reel

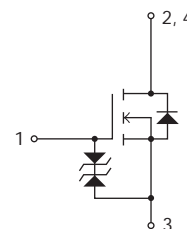
Packing Type: DL



Marking



Electrical Connection



2SK4065

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	75			V
Zero-Gate Voltage Drain Current	IDSS	VDS=75V, VGS=0V			1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=50A	47	78		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=50A, VGS=10V		4.6	6.0	mΩ
	RDS(on)2	ID=50A, VGS=4V		5.7	8.0	mΩ
Input Capacitance	Ciss	VDS=20V, f=1MHz		12200		pF
Output Capacitance	Coss			950		pF
Reverse Transfer Capacitance	Crss			730		pF
Turn-ON Delay Time	td(on)		See Fig.2		80	
Rise Time	tr			460		ns
Turn-OFF Delay Time	td(off)			930		ns
Fall Time	tf			640		ns
Total Gate Charge	Qg	VDS=35V, VGS=10V, ID=100A			220	
Gate-to-Source Charge	Qgs			40		nC
Gate-to-Drain "Miller" Charge	Qgd			50		nC
Diode Forward Voltage	VSD	IS=100A, VGS=0V		0.9	1.2	V

Fig.1 Avalanche Resistance Test Circuit

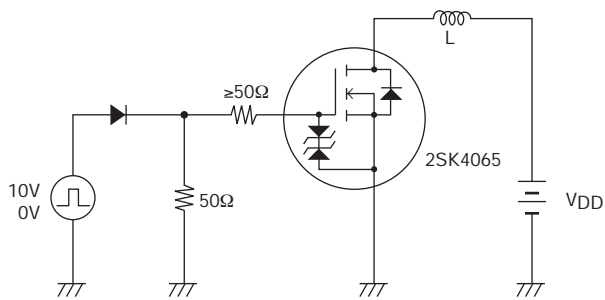
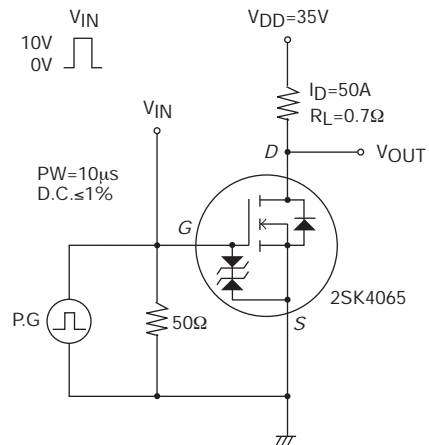
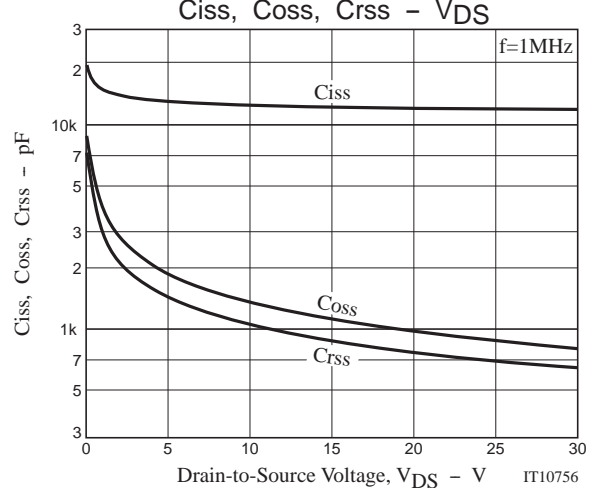
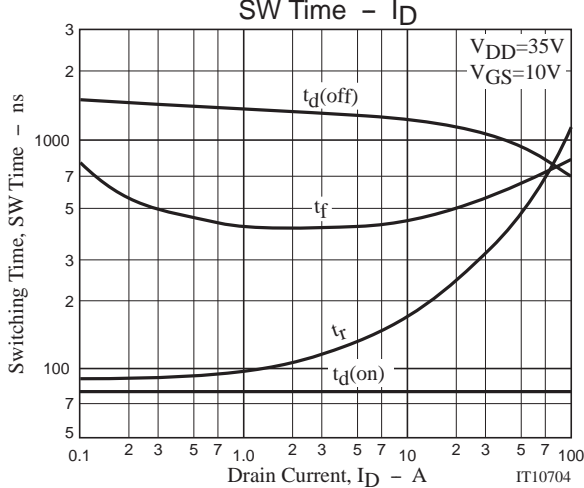
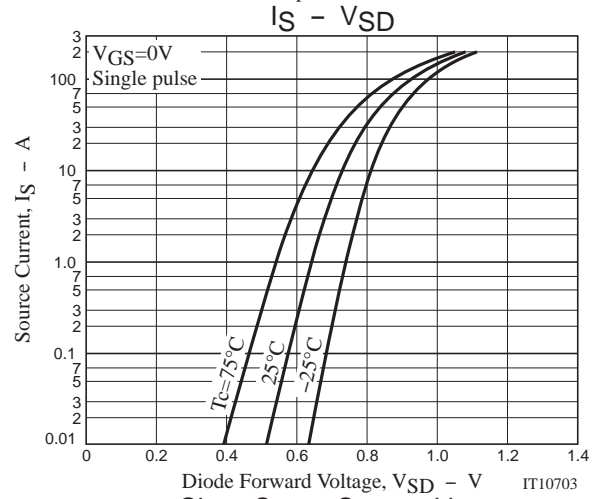
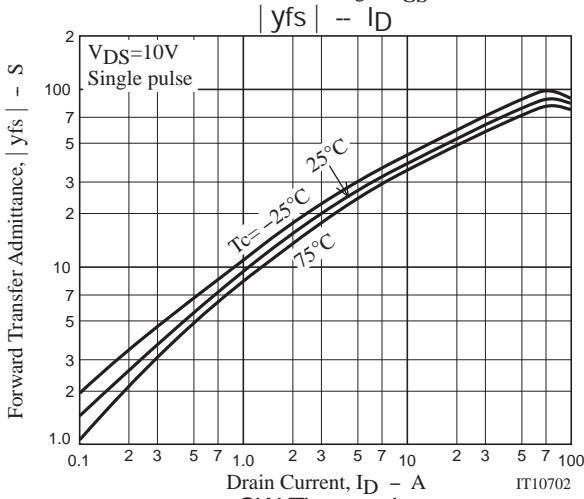
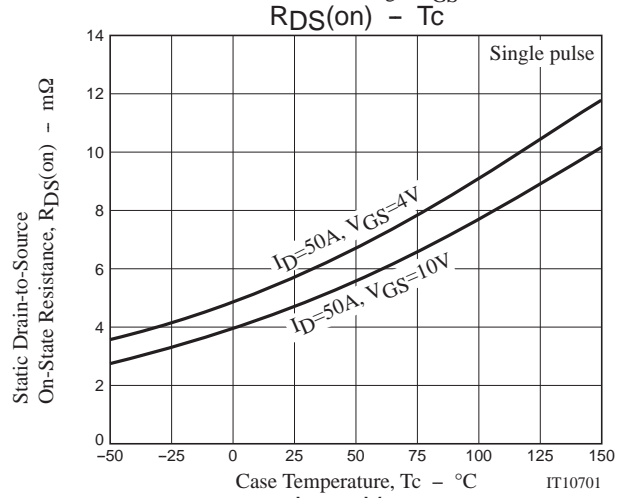
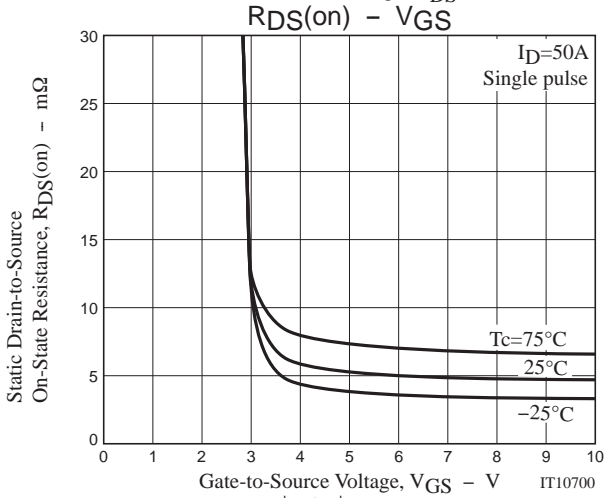
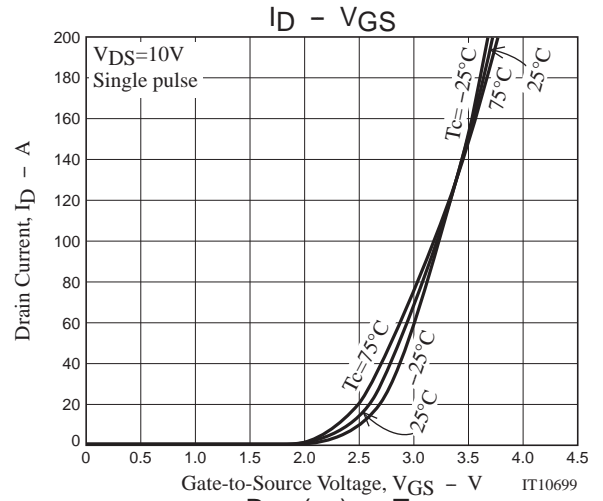
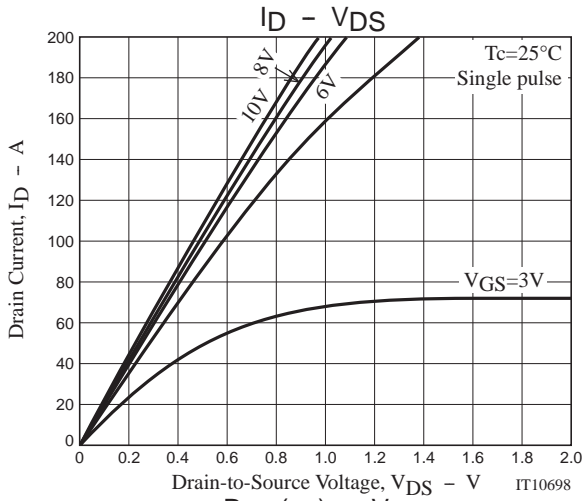


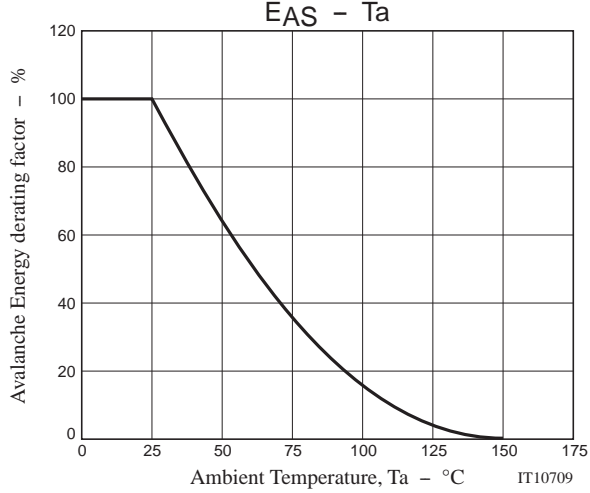
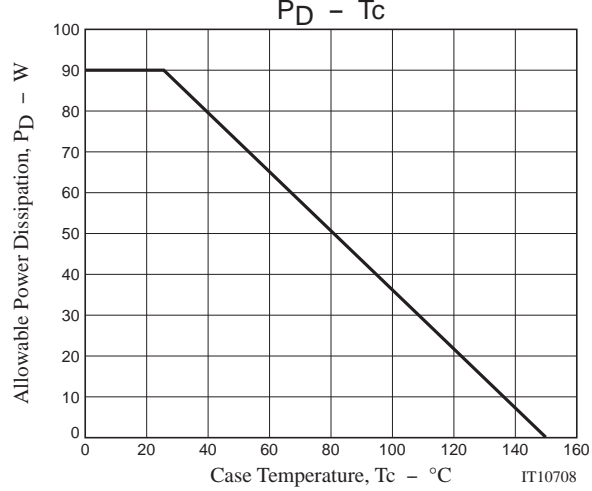
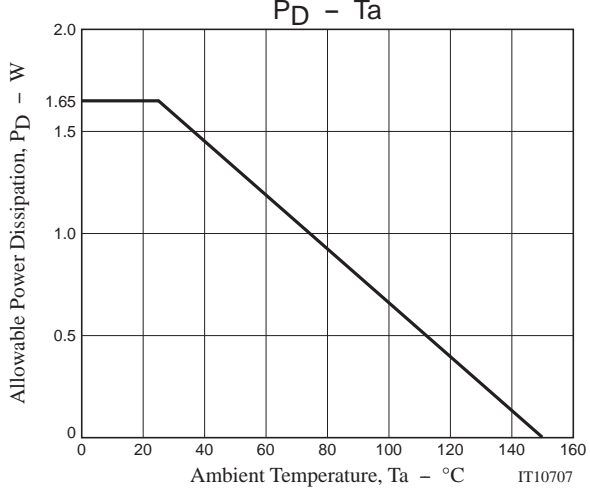
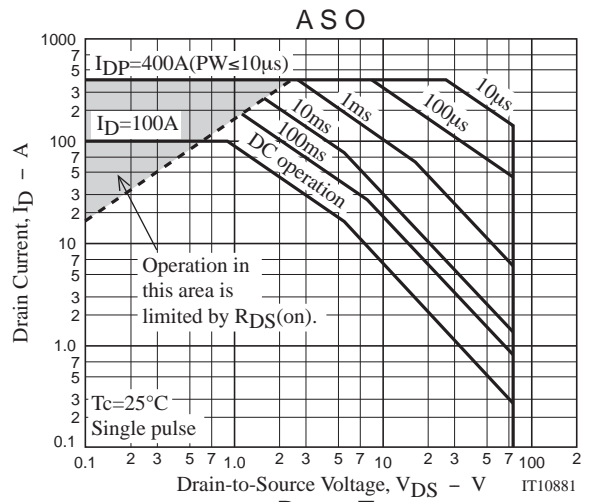
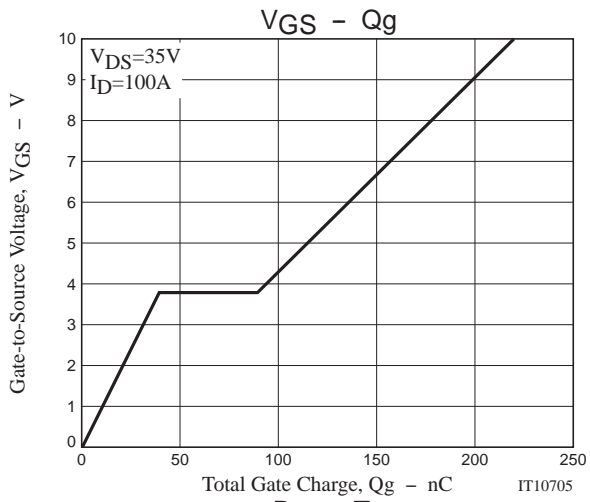
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
2SK4065-DL-1E	TO-263-2L	800pcs./reel	Pb Free





Taping Specification

2SK4065-DL-1E

1. Packing Format

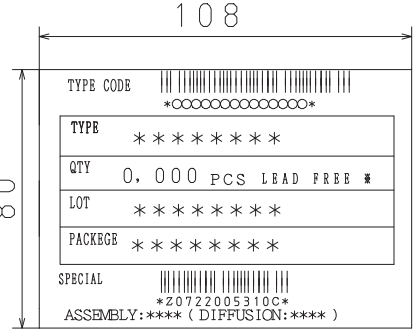
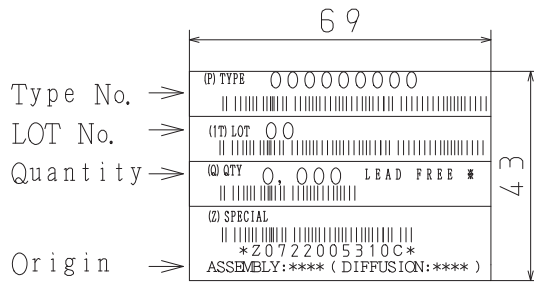
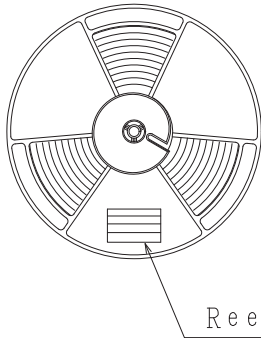
Package Name	Maximum Number of devices contained (pcs)			Packing format	
	Reel	Inner box	Outer box	Inner BOX	Outer BOX
TO-263-2L	800	1600	6400	SPD-0V0011 2 reel contained Dimensions:mm (external) 351×340×68	SPD-0V0009 4 inner boxes contained Dimensions:mm (external) 390×370×318

Reel label, Inner box label (unit:mm)

Outer box label

Packing method

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



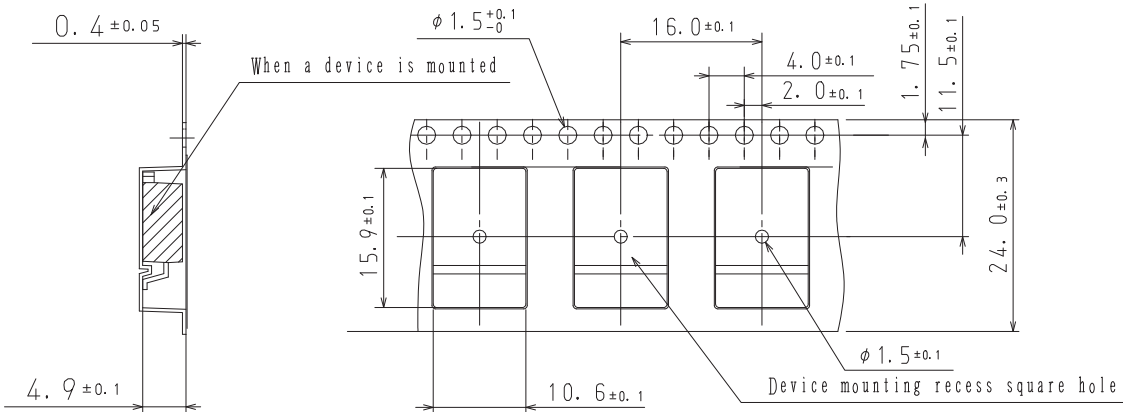
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

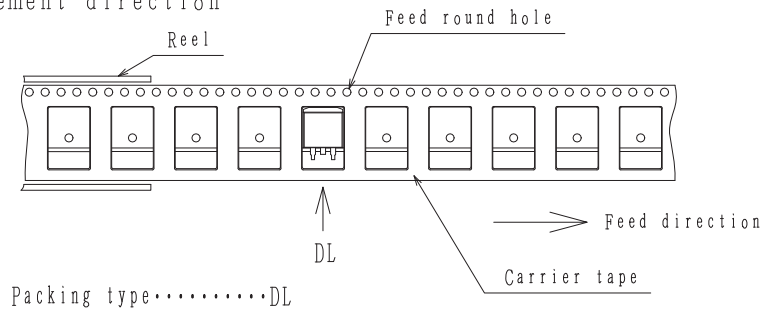
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



Note on usage : Since the 2SK4065 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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